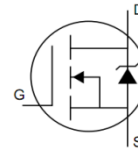




Product Summary

The ZM200N04T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

$V_{DS} = 40V$

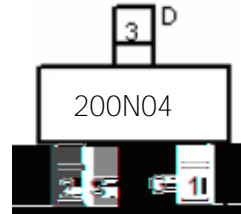


$R_{DS(ON)} = 22m$

$I_D = 5.2A$

Trench technology

$R_{DS(ON)}$ to minimize conductive loss



SOT23-3

nd Synchronous Rectifier

Part NO.	ZM200N04T
Marking	200N04
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

$T_c = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	5.0	A
	$I_{D@TC=75}$	3.8	A
	$I_{D@TC=100}$	3.2	A
Pulsed Drain Current	I_{DM}	15	A
Total Power Dissipation	$P_D@TC=25$	1.5	W
Total Power Dissipation	$P_D@TA=25$	0.7	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	80	

Fig.7 On-Resistance VS Gate Source Voltage

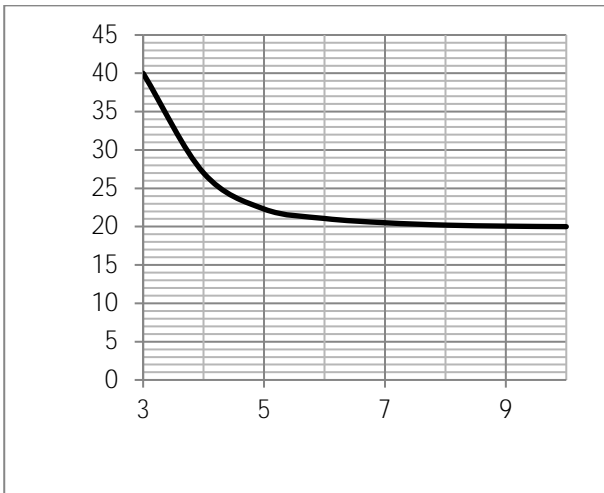


Fig.8 On-Resistance V.S Junction Temperature

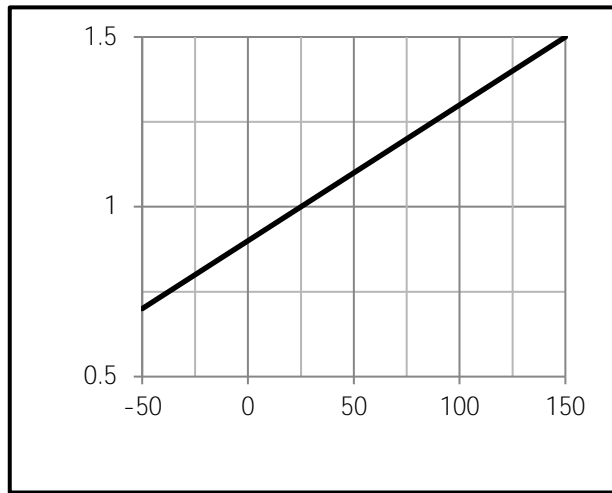


Fig.9 Switching Time Measurement Circuit

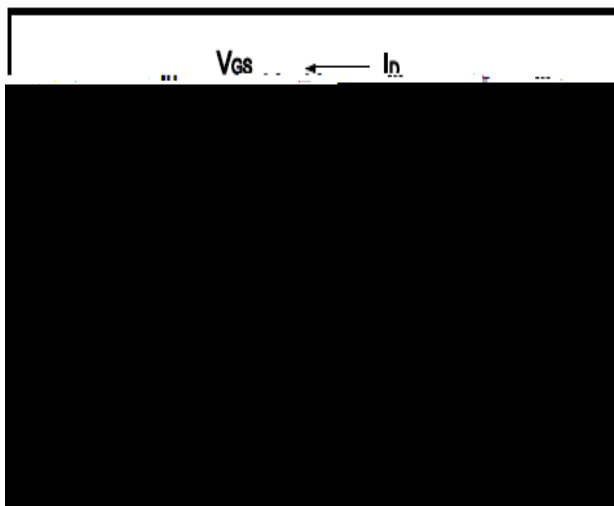


Fig.10 Gate Charge Waveform

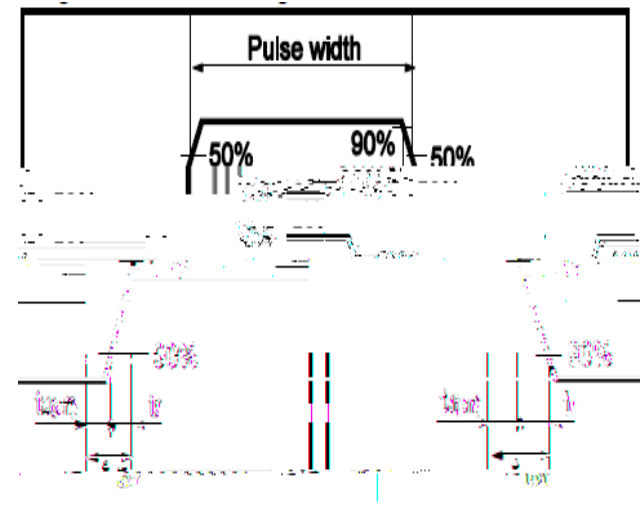


Fig.11 Avalanche Measurement Circuit

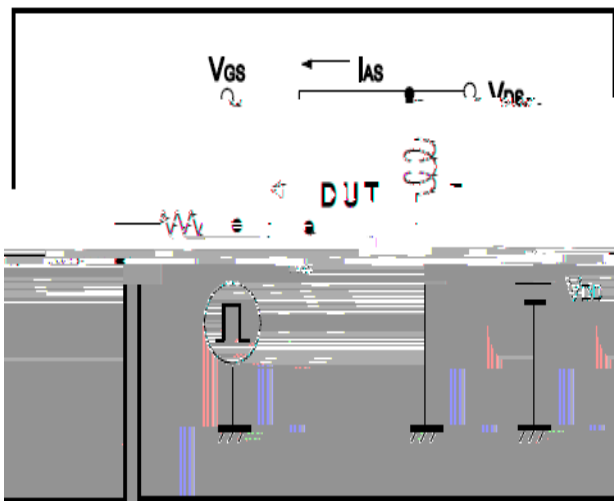


Fig.12 Avalanche Waveform

